CLEAN COPY OF ALL PENDING CLAIMS

C1 SUB D1

35. (Twice Amended) A method of fabricating a semiconductor structure, the method comprising the steps of:

providing a semiconductor substrate;

providing on said substrate a graded region incorporating a first type of strain; and

processing the graded region so as to introduce a second type of strain, the previously incorporated first type of strain reducing the process-induced second type of strain.

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39. (Twice Amended) The method of claim 45, wherein the graded region comprises Si and Ge graded to an increasing concentration of Ge, and the step of incorporating compressive strain comprises decreasing a temperature at which the graded region is grown as the Ge concentration increases in the graded region.

C3

40. (Amended) The method of claim 39, wherein the step of incorporating compressive strain comprises growing alloys of Ge_xSi_{1-x} from $x = 0$ to about $x \approx 35\%$ at 750°C, growing alloys from $x = 35$ to about $x \approx 75\%$ at between 650°C and 750°C, and growing alloys greater than 75% at 550°C.

41. (Amended) The method of claim 44, further comprising the step of planarizing at least one surface of the structure.

SUB D1 7

44. (New) The method of claim 35, further comprising the step of planarizing at least one surface of the structure.

C4

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45. (New) The method of claim 35, wherein the first type of strain is compressive strain and the second type of strain is tensile strain.